

Model	Scanning Electron Microscope FlexSEM 1000 II	Scanning Electron Microscopes SU3800	Scanning Electron Microscopes SU3900	
Magnification -	6x - 300,000x (on photo)	5x - 300,000x (on photo)		
	16x - 800,000x (on display)	7x - 800,000x (on display)		
Electron source	4.0 nm at 20 kV (SE, High Voltage, High Vacuum)	3.0 nm at 30 kV (SE, High Voltage, High Vacuum)		
	15.0 nm at 1 kV (SE, Low Voltage, High Vacuum)	15.0 nm at 1 kV (SE, Low Voltage, High Vacuum)		
	5.0 nm at 20 kV (BSE, High Voltage, Low Vacuum)	4.0 nm at 30 kV (BSE, High Voltage, Low Vacuum)		
Resolution		Pre-centered cartridge type tungsten hairpin filament		
Accelerating voltage	0.3 - 20 kV	0.3 - 30 kV		
Variable pressure	6 - 100 Pa	6 – 650 Pa		
Sample stage traverse	3-axis motorized stage	5-axis motorized stage		
	X : 0 - 50 mm	X : 0 - 100 mm	X : 0 - 150 mm	
	Y:0-40 mm	Y : 0 - 50 mm	Y : 0 - 150 mm	
	Z:5-33 mm	Z : 5 - 65 mm	Z : 5 - 85 mm	
	T : -15 - 90°	T : -20 - 90°		
	R: 360°	R : 360°		
Maximum sample size	80 mm (in diameter) 153 mm* (in diameter)	200 mm (in diameter)	300 mm (in diameter)	
Maximum sample thickness	40 mm	80 mm	130 mm	
Signal detector	SE detector			
	High sensitivity semiconductor BSE detector			
	Ultra Variable-pressure Detector (UVD)*			
Analysis system	Energy Dispersive X-ray Spectrometer (EDS)*			
		Wavelength dispersive X-ray spectrometry (WDS)*		
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